

■ Development Project of “**New Hf Precursors**” Ver.2

□ Target : **HfO₂**

Code Name	TCHf-42
① TGA _{1/2} (°C)	186
Residual mass (%)	< 3%
② DSC (°C)	286

① TGA (Thermogravimetric Analysis) : Volatility property of precursor

- TGA_{1/2} (°C) : Temperature at 50% vaporization (low temperature → high volatility)

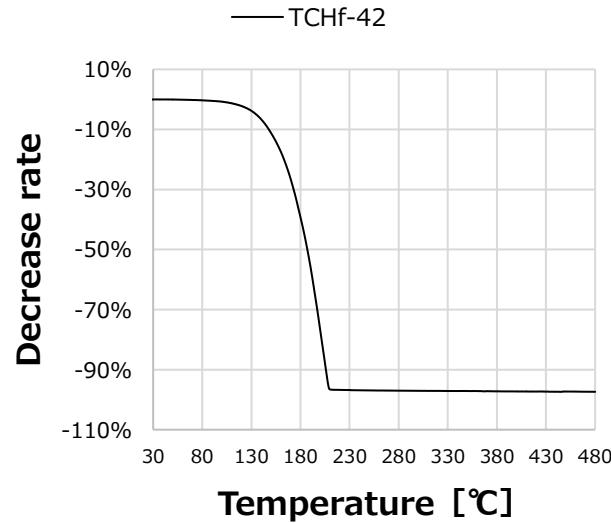
- Residual mass (%) : Residue mass after vaporization (low value → good thermal stability)

② DSC (Differential Scanning Calorimetry)
: Decomposition temperature of precursor

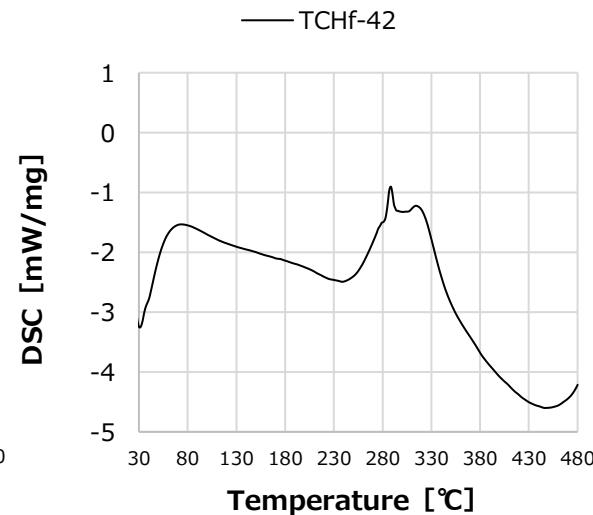
■ Vapor Pressure curve



■ TGA curve



■ DSC curve



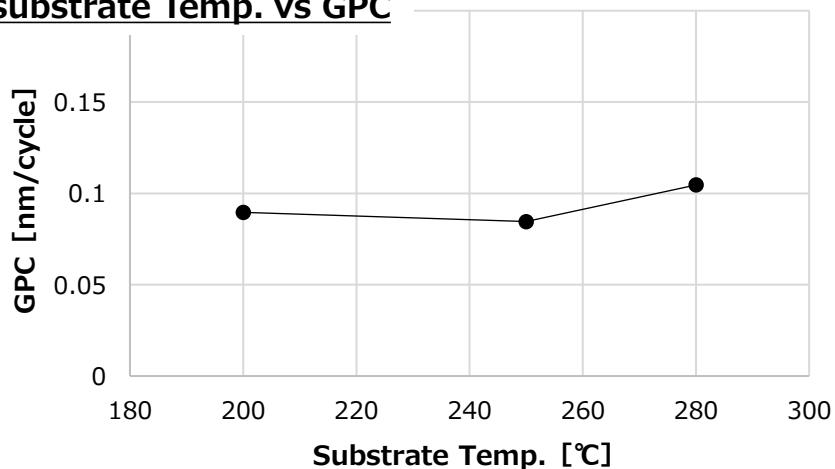
■ Collaboration “**Watty Corporation**”

□ ALD evaluation about TCHf-42

Deposition equipment	Watom-2T	
substrate	Si	
reactant	H ₂ O	
ALD window	< 280°C	
Intensity - XPS - [atm%]	Hf	26.3
	O	73.4
	other	< 0.01



■ substrate Temp. vs GPC



■ substrate Temp. vs Uniformity

